

## General Description

The WSF15N10A uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## Features

- High density cell design for ultra low  $R_{ds(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

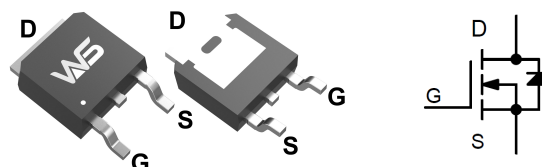
## Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

## Product Summary

BVDSS	RDSON	ID
100V	90mΩ	15A

## TO-252 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	40	A
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	40	W
	Derating factor	0.27	W/°C
EAS	Single Pulse Avalanche Energy <sup>3</sup>	20	mJ
$T_J \quad T_{STG}$	Operating Junction Temperature Range	-55 to 170	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	50	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	3.8	°C/W

**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^{\circ}\text{C}$ , $I_D=1\text{mA}$	---	0.098	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=5A$	---	90	110	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=2A$	---	110	150	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	nA
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	$\mu A$
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=5A$	3.5	---	---	S
$Q_g$	Total Gate Charge (10V)	$V_{DS}=50V, V_{GS}=10V, I_D=5A$	---	21.5	---	nC
$Q_{gs}$	Gate-Source Charge		---	3.2	---	
$Q_{gd}$	Gate-Drain Charge		---	6.0	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=6\Omega$ $I_D=1A, R_L=30\Omega$	---	11	24	ns
$T_r$	Rise Time		---	7.4	15	
$T_{d(off)}$	Turn-Off Delay Time		---	35	45	
$T_f$	Fall Time		---	9.1	12	
$C_{iss}$	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$	---	730	980	pF
$C_{oss}$	Output Capacitance		---	37	55	
$C_{rss}$	Reverse Transfer Capacitance		---	27	35	

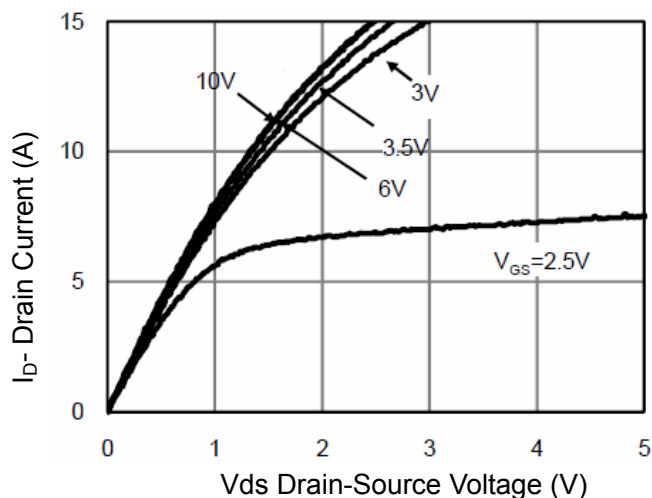
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	10	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=10A, T_J=25^{\circ}\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=10A, dI/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	17	21	61	nS
$Q_{rr}$	Reverse Recovery Charge		61	97	113	nC

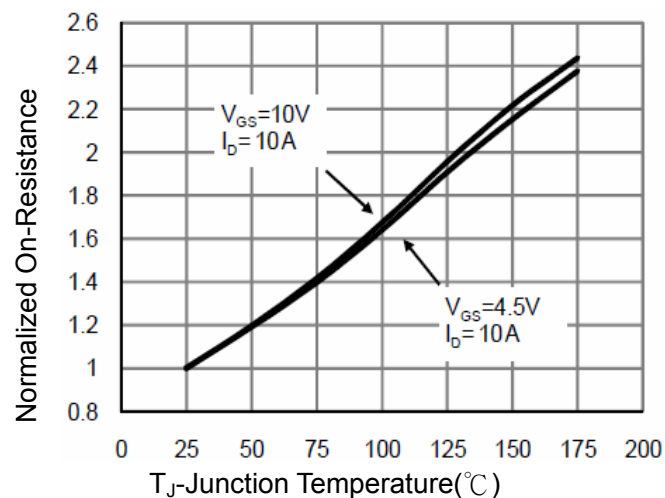
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_G=25$

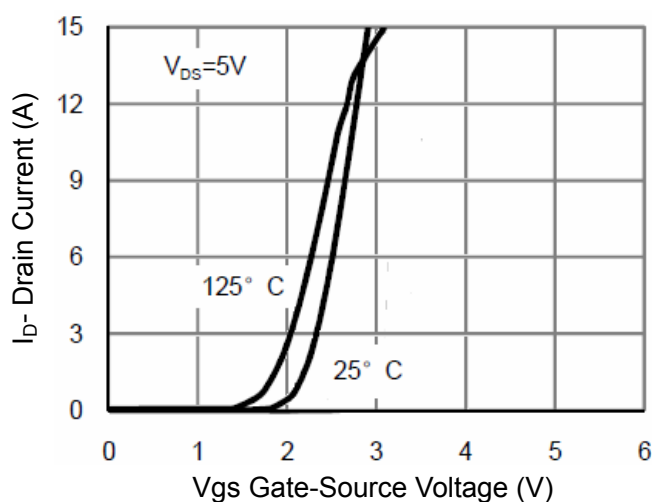
## Typical Characteristics



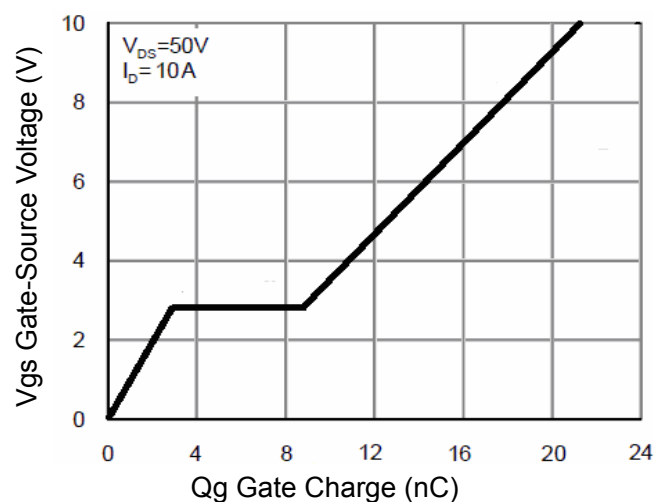
**Figure 1 Output Characteristics**



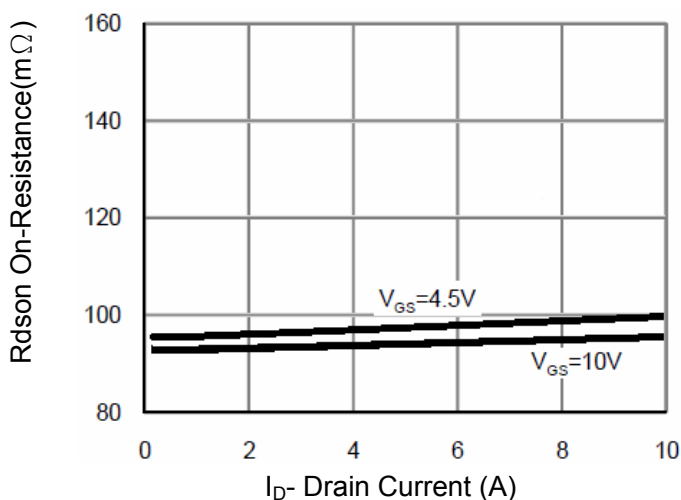
**Figure 4 Rdson-Junction Temperature**



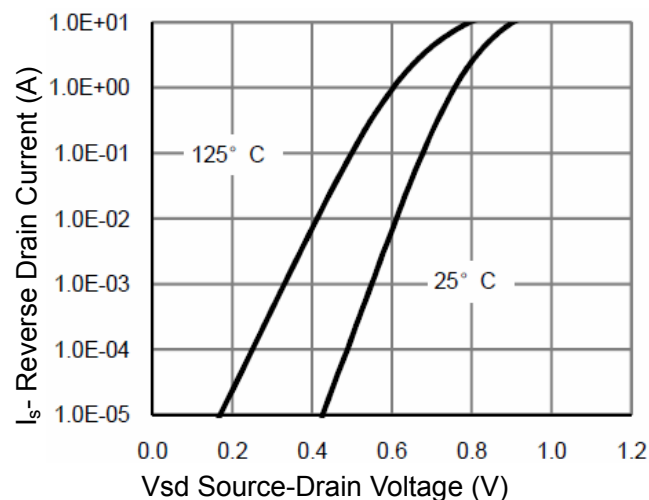
**Figure 2 Transfer Characteristics**



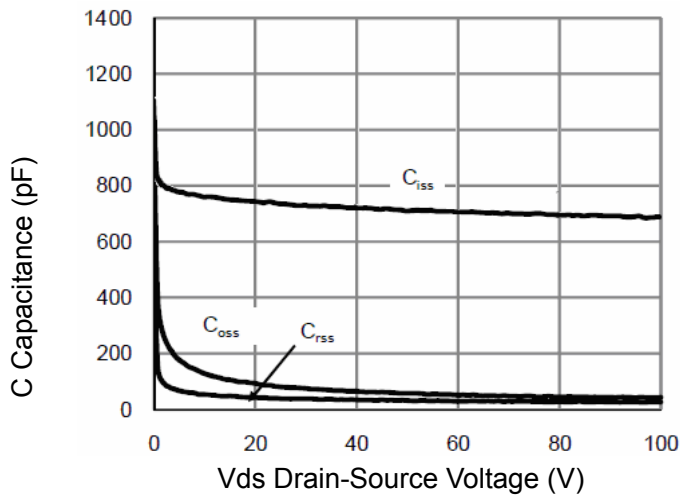
**Figure 5 Gate Charge**



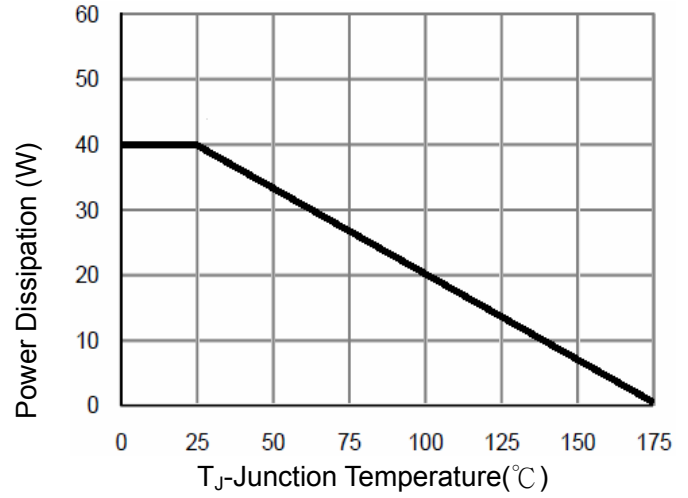
**Figure 3 Rdson- Drain Current**



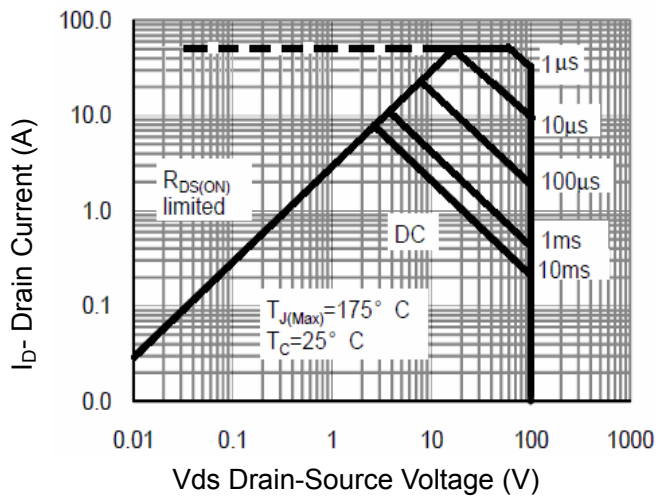
**Figure 6 Source- Drain Diode Forward**



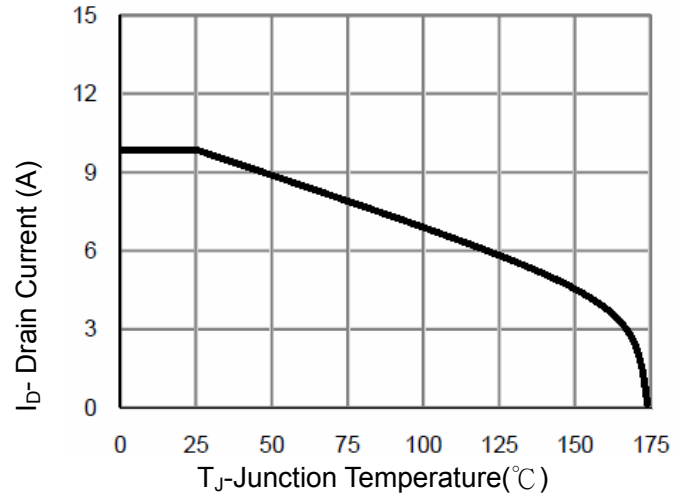
**Figure 7 Capacitance vs Vds**



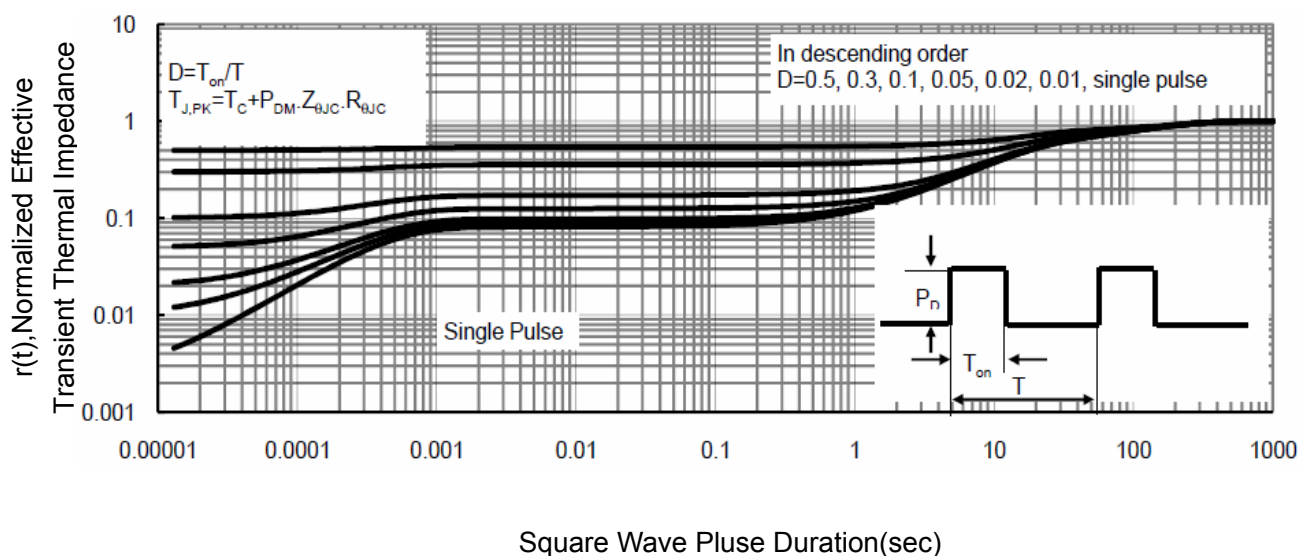
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**



**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

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